IRF630F

N-channel mosfet transistor

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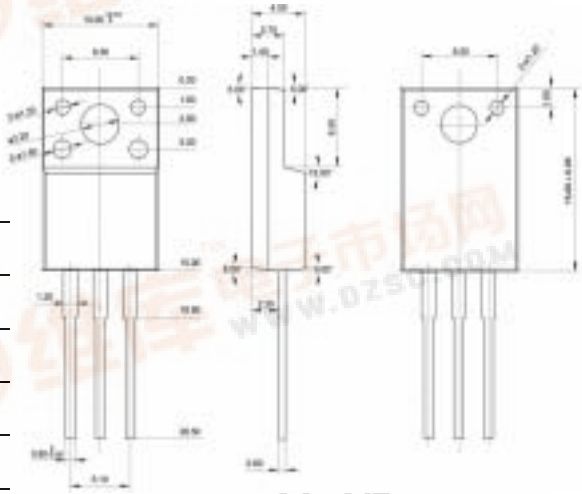
◆ Features

- With TO-220F package
- Low on-stateand thermal resistance
- Fast switching
- V_{DSS}=200V; $R_{DS(ON)}$≤0.4Ω;I_D=9A
- 1.gate 2.drain 3.source



TO-220F

◆ Absolute Maximum Ratings Tc=25℃

SYMBOL	PARAMETER	RATING	UNIT
V_{DSS}	Drain-source voltage (V_{GS}=0)	200	V
V_{GS}	Gate-source voltage	±20	V
I_D	Drain Current-continuous@ T_C=25℃	9	A
P_{tot}	Total Dissipation@TC=25℃	35	W
T_j	Operating Junction temperature	150	℃
T_{stg}	Storage temperature	-65~150	℃

◆ Electrical Characteristics Tc=25℃

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS}=0; I_D=0.25mA	200		V
$V_{GS(TH)}$	Gate threshold voltage	V_{DS}= V_{GS}; I_D=1mA	2	4	V
$R_{DS(ON)}$	Drain-source on-stage resistance	V_{GS}=10V; I_D=5.4A		400	mΩ
I_{GSS}	Gate source leakage current	V_{GS}=±20V;V_{DS}=0		±100	nA
I_{DSS}	Zero gate voltage drain current	V_{DS}=200V; V_{GS}=0		10	uA
V_{SD}	Diode forward voltage	I_F=9A; V_{GS}=0		1.2	V